

isc Silicon NPN Power Transistors

BUP23B/C

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V$ (Min)-BUP23B
450V (Min)-BUP23C
- High Switching Speed

APPLICATIONS

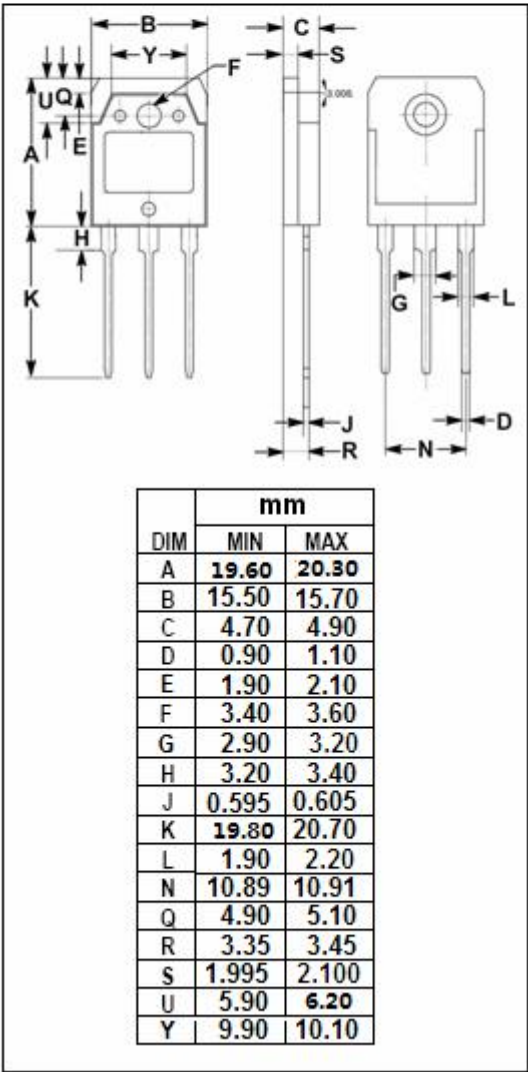
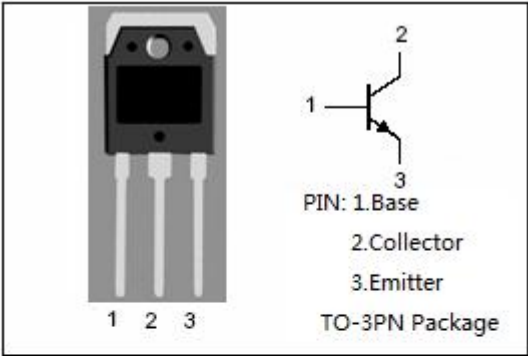
- Designed for use in converters, inverters, switching regulators, motor control systems etc.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CES}	Collector- Emitter Voltage($V_{BE}=0$)	BUP23B	750	V
		BUP23C	850	
V_{CEO}	Collector-Emitter Voltage	BUP23B	400	V
		BUP23C	430	
V_{EBO}	Emitter-Base Voltage		9	V
I_C	Collector Current- Continuous		15	A
I_{CM}	Collector Current-Peak		30	A
I_B	Base Current- Continuous		6	A
I_{BM}	Base Current-Peak		9	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$		175	W
T_J	Junction Temperature		150	$^{\circ}C$
T_{stg}	Storage Temperature Range		-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal Resistance,Junction to Case	0.7	$^{\circ}C/W$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	BUP23B	$I_C= 50mA ; I_B= 0$	400			V
		BUP23C		450			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	BUP23B	$I_C= 10A; I_B= 1.33A$			1.5	V
		BUP23C	$I_C= 10A; I_B= 1.67A$			1.5	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	BUP23B	$I_C= 10A; I_B= 1.33A$			1.5	V
		BUP23C	$I_C= 10A; I_B= 1.67A$			1.5	
I_{CES}	Collector Cutoff Current		$V_{CE}= V_{CESmax} ; V_{BE}= 0$			1	mA
I_{EBO}	Emitter Cutoff Current		$V_{EB}= 9V ; I_C= 0$			10	mA
h_{FE}	DC Current Gain		$I_C= 1A ; V_{CE}= 5V$		25		
Switching Times, Resistive Load							
t_{on}	Turn-On Time		For BUP23B $I_C= 10A ; I_{B1}= -I_{B2}= 1.33A$ For BUP23C $I_C= 10A ; I_{B1}= -I_{B2}= 1.67A$		0.7		μs
t_{stg}	Storage Time				2.0		μs
t_f	Fall Time				0.27		μs